

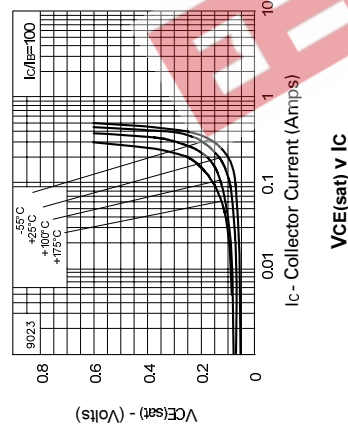
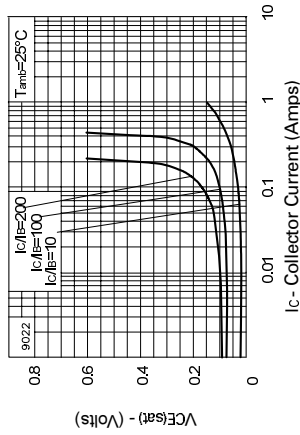
# FZT694B

# SOT223 NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

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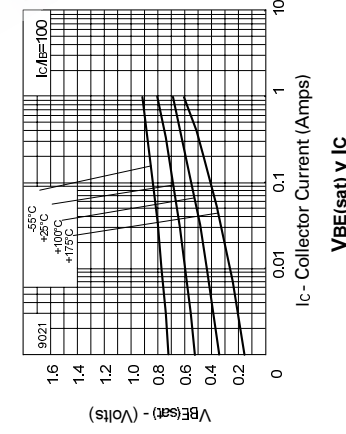
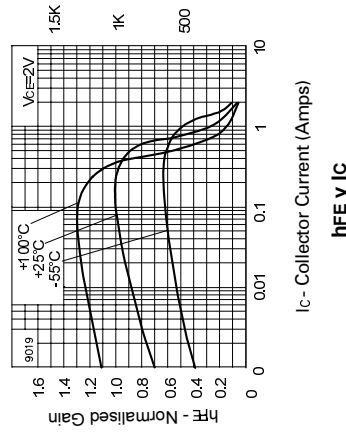
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## TYPICAL CHARACTERISTICS



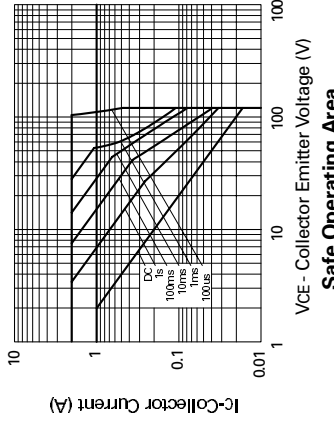
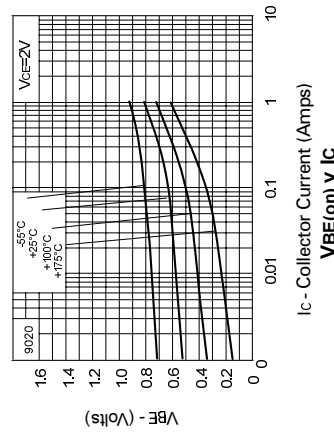
VCE(sat) v IC

VCE(sat) v IC



hFE v IC

VBE(sat) v IC



IC - Collector Current (Amps)

VCE - Collector Emitter Voltage (V)

Safe Operating Area

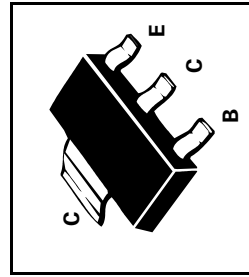
## FEATURES

- \* High  $V_{CE0}$  / Very Low Saturation Voltage
- \* Gain of 400 at  $I_C=200\text{mA}$

## APPLICATIONS

- \* Darlington replacement
- \* Relay / solenoid driver

PARTMARKING DETAIL - FZT694B



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CB0}$	120	V
Collector-Emitter Voltage	$V_{CE0}$	120	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Peak Pulse Current	$I_{CM}$	2	A
Continuous Collector Current	$I_C$	1	A
Power Dissipation $T_{amb}=25^\circ\text{C}$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	120			V	$I_C=100\mu\text{A}$
	$V_{(BR)CEO}$	120			V	$I_C=10\text{mA}^*$
	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		0.1		$\mu\text{A}$	$V_{CB}=100\text{V}$
Emitter Cut-Off Current	$I_{EBO}$		0.1		$\mu\text{A}$	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25		V	$I_C=100\text{mA}, I_B=0.5\text{mA}^*$
	$V_{CE(sat)}$		0.5		V	$I_C=400\text{mA}, I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9		V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.9		V	$I_C=1\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500				$I_C=100\text{mA}, V_{CE}=2\text{V}^*$
	$h_{FE}$	400				$I_C=200\text{mA}, V_{CE}=2\text{V}^*$
	$h_{FE}$	150				$I_C=400\text{mA}, V_{CE}=2\text{V}^*$
Transition Frequency	$f_T$	130			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	$C_{ibo}$		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	$C_{obo}$		9		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	$t_{on}$		80		ns	$I_C=100\text{mA}, I_B=10\text{mA}$
	$t_{off}$		2900		ns	$I_B=10\text{mA}, V_{CE}=50\text{V}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$   
Spice parameter data is available upon request for this device

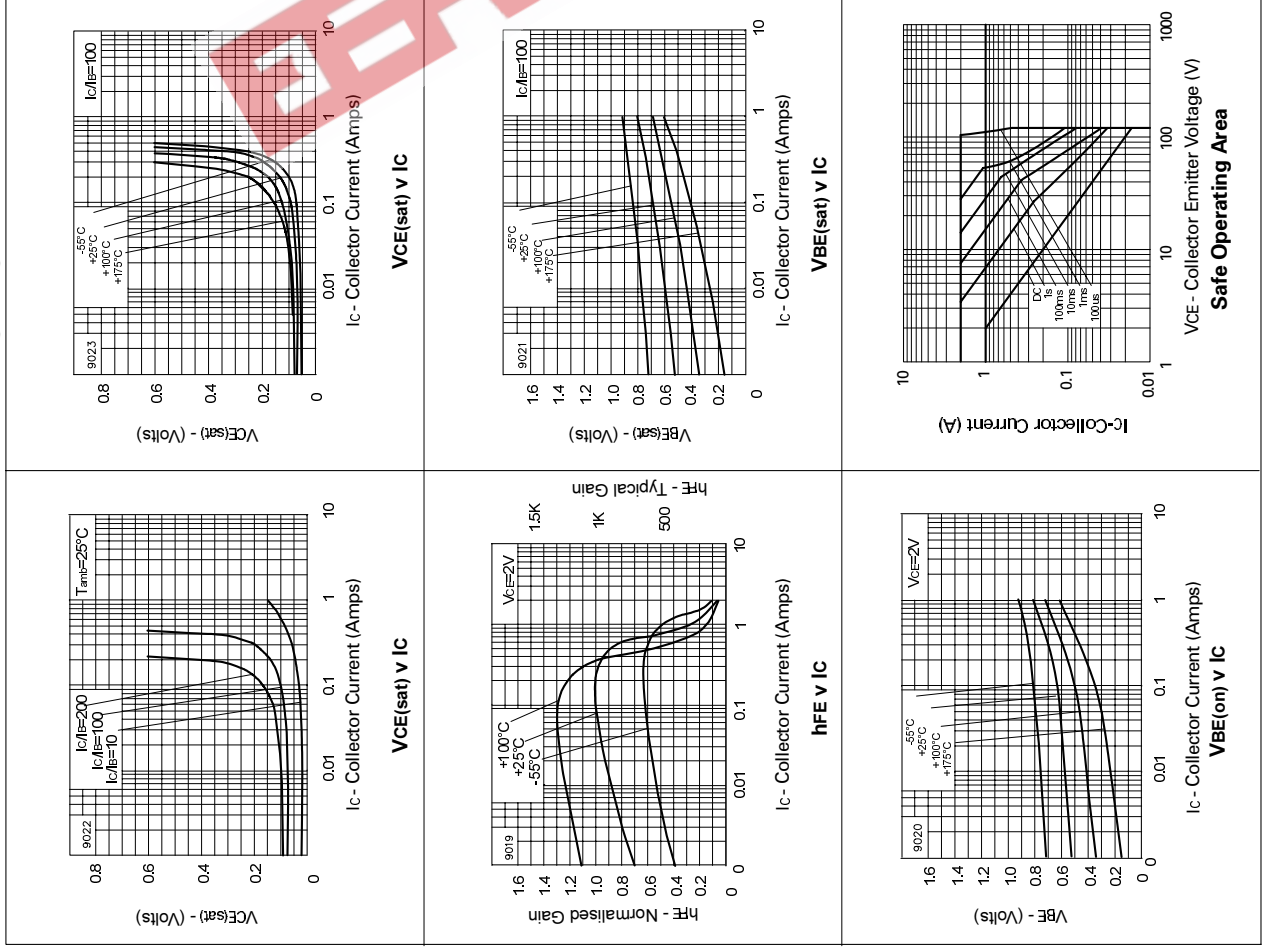
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**TYPICAL CHARACTERISTICS**

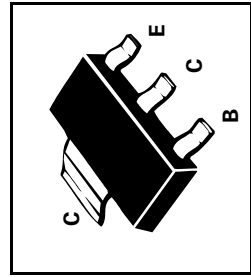


**FEATURES**

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**APPLICATIONS**

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Collector-Emitter Voltage	$V_{CEO}$	120	V
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Continuous Collector Current	$I_C$	1	A
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Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9		V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.9		V	$I_C=1\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500				$I_C=100\text{mA}, V_{CE}=2\text{V}^*$
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